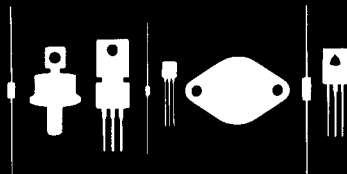


Central
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145 Adams Avenue
Hauppauge, New York 11788



1N485B
1N486B

SILICON DIODE

JEDEC DO-35 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 1N485B, 1N486B types are silicon planar diodes designed for low leakage applications.

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

	<u>SYMBOL</u>	<u>1N485B</u>	<u>1N486B</u>	<u>UNITS</u>
Peak Repetitive Reverse Voltage	V_{RRM}	200	250	V
Peak Working Reverse Voltage	V_{RWM}	180	225	V
Average Forward Current	I_O	200	200	mA
Forward Steady-State Current	I_F	500	500	mA
Peak Repetitive Forward Current	I_{FM}	600	600	mA
Peak Forward Surge Current (1.0 μ s pulse)	I_{FSM}	4.0	4.0	A
Peak Forward Surge Current (1.0s pulse)	I_{FSM}	1.0	1.0	A
Power Dissipation	P_D	500	500	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +200		$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

<u>SYMBOL</u>	<u>TEST CONDITIONS</u>	<u>1N485B</u>		<u>1N486B</u>		<u>UNITS</u>
		<u>MIN</u>	<u>MAX</u>	<u>MIN</u>	<u>MAX</u>	
BV_R	$I_R = 100\mu\text{A}$	200		250		V
I_R	$V_R = \text{Rated } V_{RWM}$		25		50	nA
I_R	$V_R = \text{Rated } V_{RWM}, T_A = 150^\circ\text{C}$		5.0		10	μA
V_F	$I_F = 100\text{mA}$		1.0		1.0	V

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